

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

# 2SA1832F

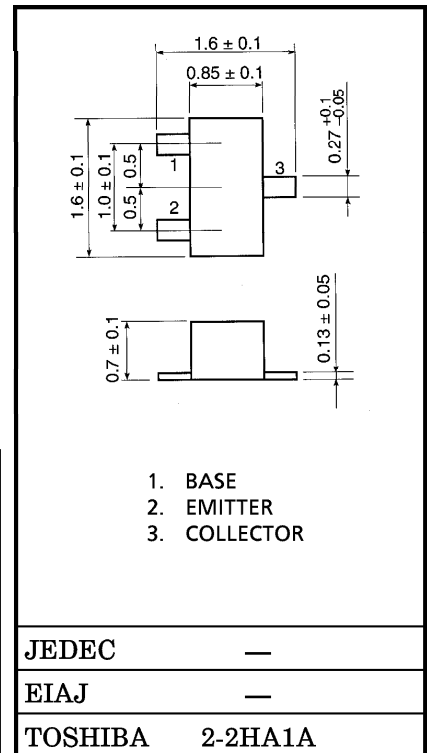
AUDIO FREQUENCY GENERAL PURPOSE AMPLIFIER APPLICATIONS

Unit in mm

- High Voltage and High Current  
:  $V_{CEO} = -50\text{ V}$ ,  $I_C = -150\text{ mA}$  (max.)
- Excellent  $h_{FE}$  Linearity  
:  $h_{FE}(I_C = -0.1\text{ mA}) / h_{FE}(I_C = -2\text{ mA}) = 0.95$  (typ.)
- High  $h_{FE}$  :  $h_{FE} = 120\sim 400$
- Complementary to 2SC4738F
- Small Package

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-150	mA
Base Current	$I_B$	-30	mA
Collector Power Dissipation	$P_C$	100	mW
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55~125	$^\circ\text{C}$

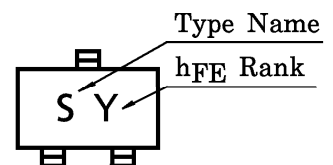


ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -50\text{ V}$ , $I_E = 0$	—	—	-0.1	$\mu\text{A}$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -5\text{ V}$ , $I_C = 0$	—	—	-0.1	$\mu\text{A}$
DC Current Gain	$h_{FE}$ (Note)	$V_{CE} = -6\text{ V}$ , $I_B = -2\text{ mA}$	120	—	400	
Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})$	$I_C = -100\text{ mA}$ , $I_B = -10\text{ mA}$	—	-0.1	-0.3	V
Transition Frequency	$f_T$	$V_{CE} = -10\text{ V}$ , $I_C = -1\text{ mA}$	80	—	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10\text{ V}$ , $I_E = 0$ , $f = 1\text{ MHz}$	—	4	7	pF

(Note) :  $h_{FE}$  Classification Y (Y) : 120~240, GR (G) : 200~400  
( ) Marking Symbol

MARKING



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